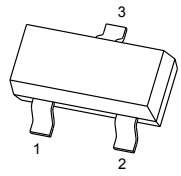
BSS84

SOT-23 Plastic-Encapsulate MOSFETS

-50V P-Channel MOSFET

$V_{(BR)DSS}$	$R_{DS(on)}$MAX	I_D
-50V	8Ω @ -10V	-130mA
	10Ω@ -5V	

SOT-23



1. GATE
2. SOURCE
3. DRAIN

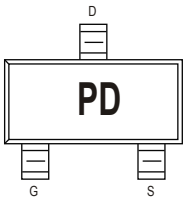
FEATURE

- Energy Efficient
- Low Threshold Voltage
- High-speed Switching
- Miniature Surface Mount Package Saves Board Space

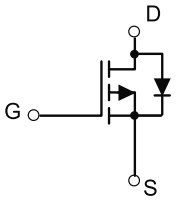
APPLICATION

- DC−DC converters,load switching, power management in portable and battery −powered products such as computers, printers, cellular and cordless telephones.

MARKING



Equivalent circuit



PACKAGE SPECIFICATIONS

Package	Reel Size	Reel DIA. (mm)	Q'TY/Reel (pcs)	Box Size (mm)	QTY/Box (pcs)	Carton Size (mm)	Q'TY/Carton (pcs)
SOT-23	7'	330	3000	203×203×195	45000	438×438×220	180000

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-50	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current	I_D	-0.13	A
Pulsed Drain Current (note 1) @tp <10 μs	I_{DM}	-0.52	A
Power Dissipation	P_D	225	mW
Thermal Resistance from Junction to Ambient (note 2)	$R_{\theta JA}$	556	℃/W
Junction Temperature	T_J	150	℃
Storage Temperature	T_{STG}	-55~+150	℃
Maximum Lead Temperature for Soldering Purposes , Duration for 5 Seconds	T_L	260	℃

The above data are for reference only.

MOSFET ELECTRICAL CHARACTERISTICS

T_a=25℃ unless otherwise specified

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
STATIC CHARACTERISTICS						
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D =-250μA	-50			V
Zero gate voltage drain current	I_{DSS}	V_{DS} =-50V,V_{GS} = 0V			-15	μA
		V_{DS} =-25V,V_{GS} = 0V			-0.1	μA
Gate-body leakage current	I_{GSS}	V_{GS} =±20V, V_{DS} = 0V			±5	μA
Gate threshold voltage (note 3)	$V_{GS(th)}$	V_{DS} =V_{GS}, I_D =-250μA	-0.9	-1.6	-2	V
Drain-source on-resistance (note 3)	$R_{DS(on)}$	V_{GS} =-5V, I_D =-0.1A		5.8	10	Ω
		V_{GS} =-10V, I_D =-0.1A		4.5	8	Ω
Forward transconductance (note 1)	g_{FS}	V_{DS}=-25V; I_D=-100mA	50			mS
DYNAMIC CHARACTERISTICS (note 4)						
Input capacitance	C_{iss}	V_{DS} =5V,V_{GS} =0V,f =1MHz		30		pF
Output capacitance	C_{oss}			10		pF
Reverse transfer capacitance	C_{rss}			5		pF
SWITCHING CHARACTERISTICS (note 4)						
Turn-on delay time	$t_{d(on)}$	V_{DD}=-15V, R_L=50Ω, I_D =-2.5A		2.5		ns
Turn-on rise time	t_r			1		ns
Turn-off delay time	$t_{d(off)}$			16		ns
Turn-off fall time	t_f			8		ns
SOURCE−DRAIN DIODE CHARACTERISTICS						
Continuous Current	I_S				-0.13	A
Pulsed Current	I_{SM}				-0.52	A
Diode forward voltage (note 3)	V_{SD}	I_S=-0.13A, V_{GS} = 0V			-2.2	V

Notes :

1. Repetit e rating : Pulse width limited by junction temperature.
2. Surface m nted on FR4 board , t≤10s.
3. Pulse Test : Pulse Width≤300μs, Duty Cycle≤2%.
4. Guaranteed by design, not subject to producting.

Typical Characteristics

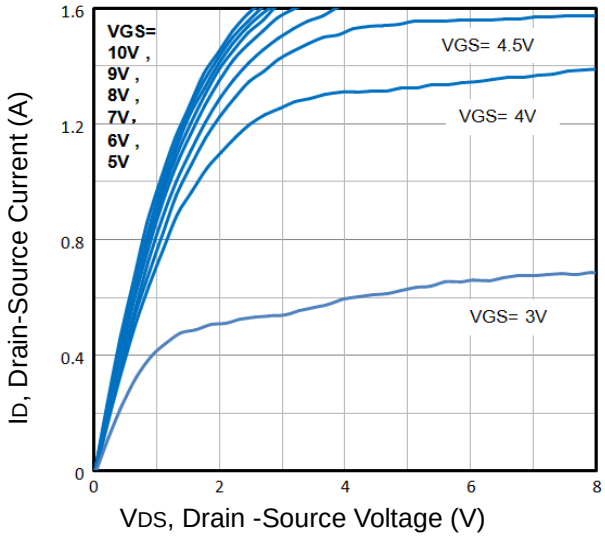


Fig1. Typical Output Characteristics

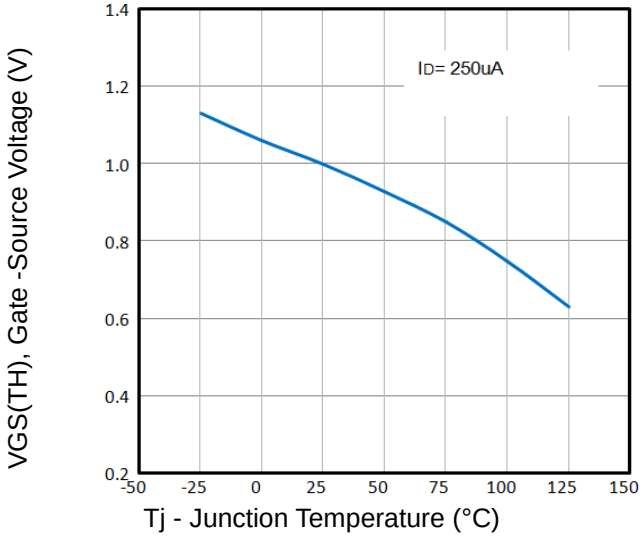


Fig2. Normalized Threshold Voltage Vs. Temperature

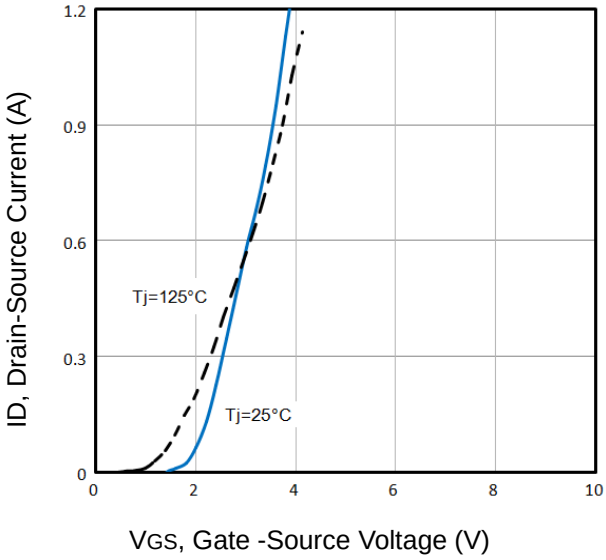


Fig3. Typical Transfer Characteristics

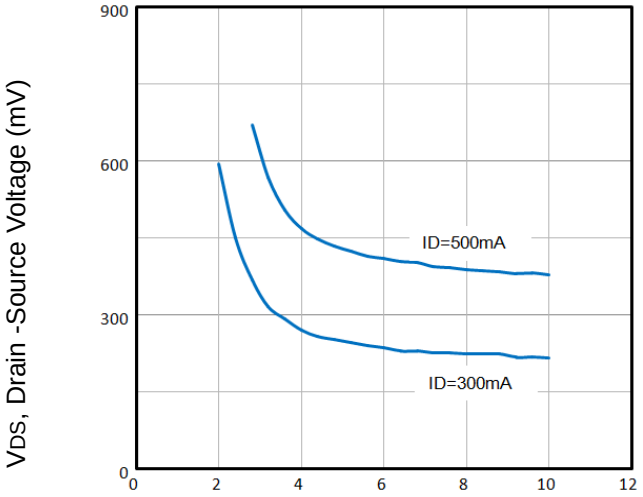


Fig4. Drain -Source Voltage vs Gate -Source Voltage

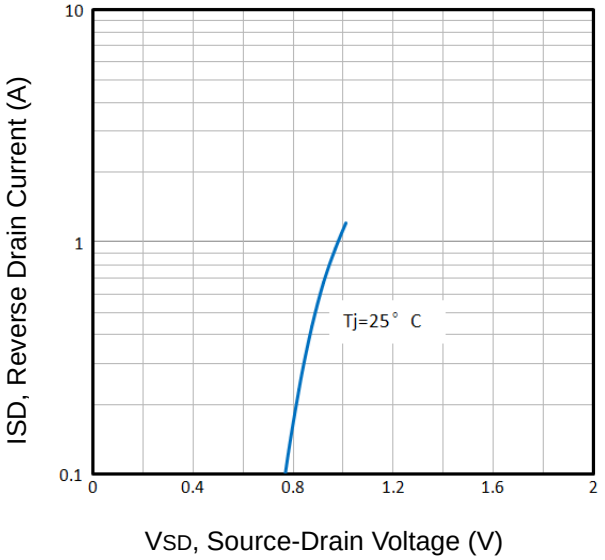


Fig5. Typical Source-Drain Diode Forward Voltage

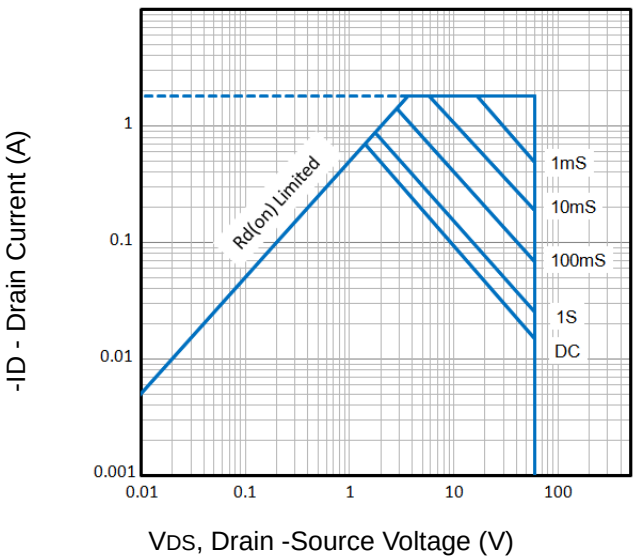


Fig6. Maximum Safe Operating Area

Typical Characteristics

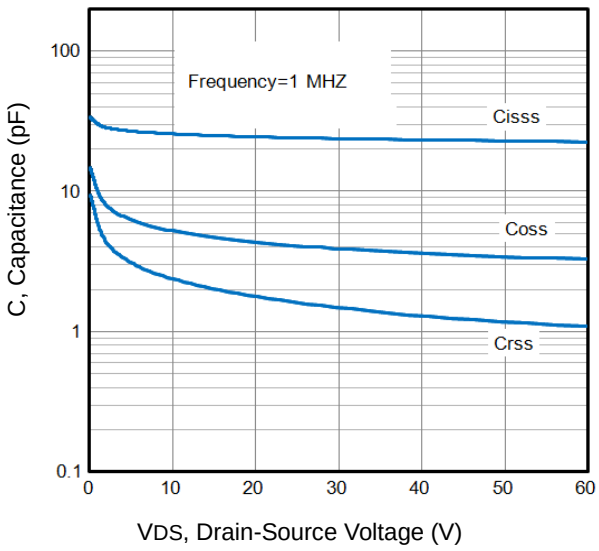


Fig7. Typical Capacitance Vs. Drain-Source Voltage

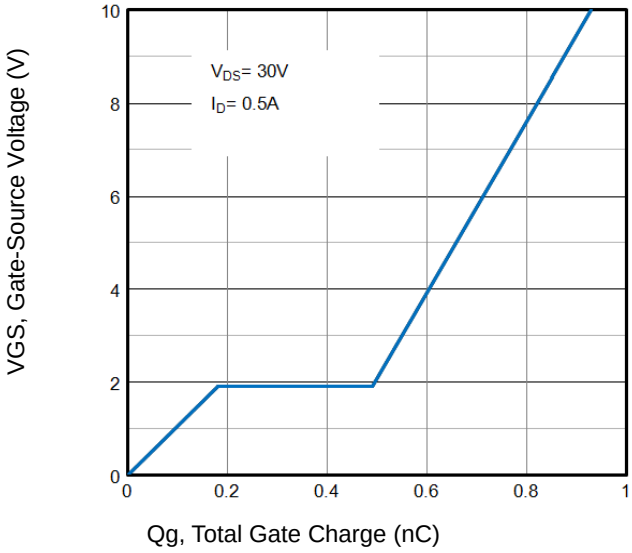


Fig8. Typical Gate Charge Vs. Gate-Source Voltage

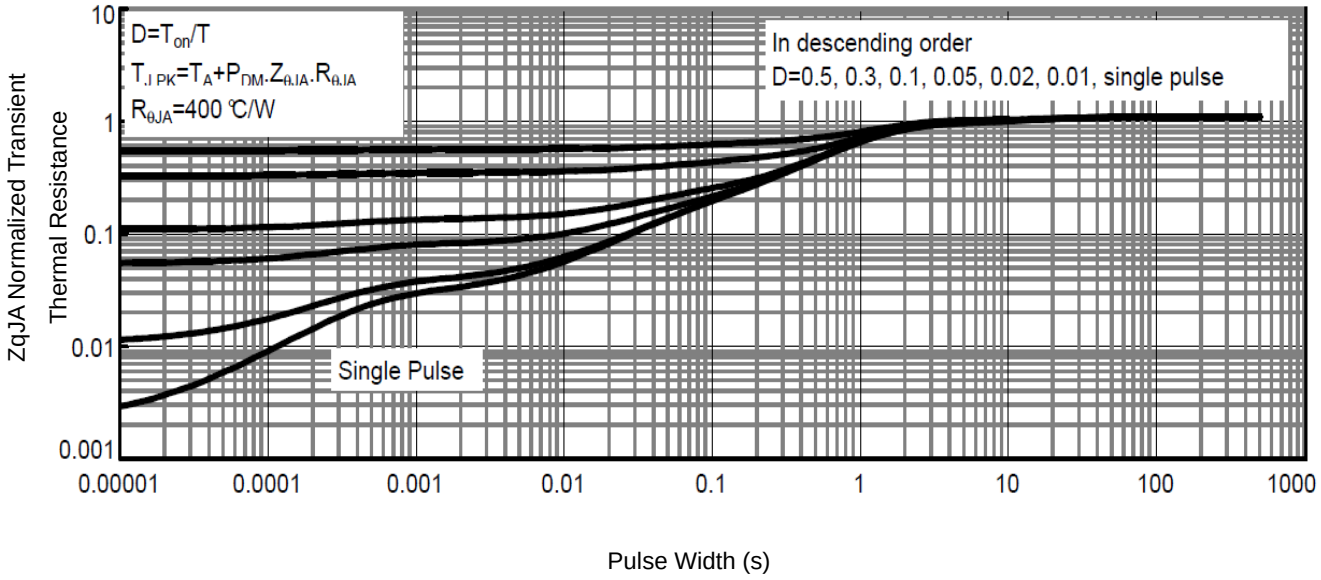


Fig9. Normalized Maximum Transient Thermal Impedance

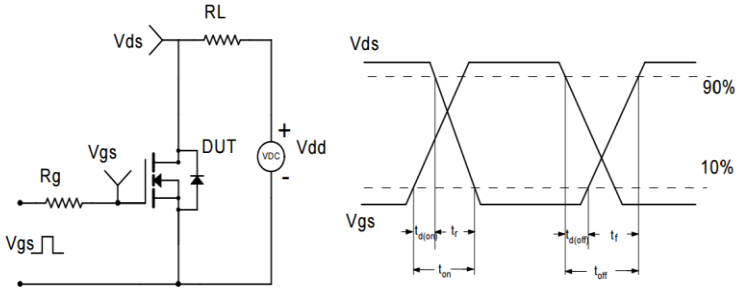
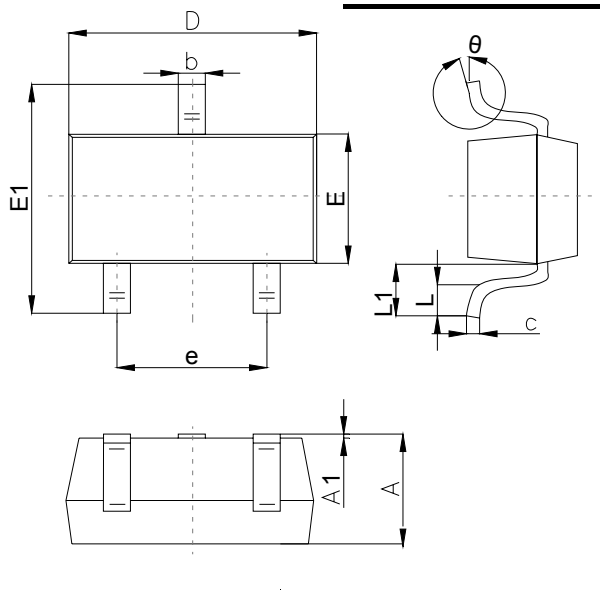


Fig10. Switching Time Test Circuit and waveforms

The curve above is for reference only.

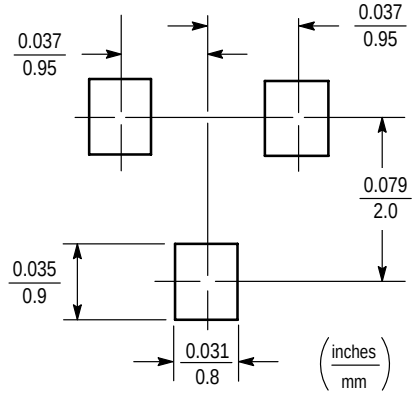
Outlitne Drawing

SOT-23 Package Outline Dimensions



Symbol	Dimensions In Millimeters		
	Min	Typ	Max
A	1.00		1.40
A1			0.10
b	0.35		0.50
c	0.10		0.20
D	2.70	2.90	3.10
E	1.40		1.60
E1	2.4		2.80
e		1.90	
L	0.10		0.30
L1	0.4		
θ	0°		10°

Suggested Pad Layout



Note:
1.Controlling dimension:in/millimeters.
2.General tolerance: ±0.05mm.
3.The pad layout is for reference purposes only.

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